NSN 5962-01-420-4648

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Test Data Document:



View Online at https://aerobasegroup.com/nsn/5962-01-420-4648

Body Length:
0.358 inches
Body Width:
0.358 inches
Body Height:
0.100 inches
Maximum Power Dissipation Rating:
500.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Pacer dawn
Features Provided:
Burn in and electrostatic sensitive and hermetically sealed and programmed and positive outputs and monolithic
Inclosure Material:
Ceramic and glass
Inclosure Configuration:
Leadless flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Criticality Code Justification:
Cbbl
Case Outline Source And Designator:
C-2 mil-m-38510
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, programmed (pal 16r8a-2)
Voltage Rating And Type Per Characteristic:
7.0 volts power source
Time Rating Per Chacteristic:
25.00 nanoseconds propagation delay time, high to low level output and 25.00 nanoseconds propagation delay time, low to high level
output
Memory Device Type:
Pal
Special Features:
Altered item, made from device p/n 81036122x, cage 67268, microcircuit, memory, programmable logic, monolithic silicon

96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal 	Type	And	Quantity:
ı C i illili ai	IYPE	Allu	Qualitity.

20 leadless

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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